Docket No.: 8733.330.00

Declaration, Power of Attorney and Petition

WE (I) the undersigned inventor(s), hereby declare(s) that:

My residence, post office address and citizenship are as stated below next to my name,

We (I) believe that we are (I am) the original, first, and joint (sole) inventor(s) of the subject matter which is claimed and for which a patent is sought on the invention entitled

Polysilicon Thin Film Transistor Used in a Liquid Crystal Display and the Fabricating Method

is attached he	ereto.			
was filed on	November 27, 2000			
	as Application Serial	No	:- 	
	and amended on			
ication, including the	that we (I) have review claims, as amended by a e the duty to disclose in	any amendment referred	I to above.	
()	n Section 1.56 of Title 3			the patentaon
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We (I) hereby claim the benefit under 35 U.S.C. §120 of any United States application(s), or §365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of 35 U.S.C. §112, I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR §1.56 which became available between the filing date of the prior application and the national or PCT International filing date of this application.

Application Serial No.

Date

Filing Date

Status (pending, patented, abandoned)

And we (I) hereby appoint Song K. Jung, Reg. No. 35,210; John M. Kelly, Reg. No. 33,920; Kenneth D. Springer, Reg. No. 39,843; and Rebecca A. Goldman, Reg. No. 41,786 and as our (my) attorneys, with full powers of substitution and revocation, to prosecute this application and to transact all business in the Patent Office connected therewith; and we (I) hereby request that all correspondence regarding this application be sent to Song K. Jung of Long Aldridge & Norman LLP, Attorneys At Law, 6th Floor, 701 Pennsylvania Avenue, N.W., Washington, D.C. 20004.

We (I) declare that all statements made herein of our (my) own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

AHN, Byung-Chul	Residence: 145-22 Hyonggok-dong,		
NAME OF FIRST SOLE INVENTOR	Kumi-shi, Kyoungsangbuk-do, 730-040,		
	Republic of Korea		
hyung chul Sh-	Citizen of: Republic of Korea		
Signature of Inventor	Post Office Address: Same As Above		
Dec 22, 2000			
Date			
	Residence:		
NAME OF SECOND INVENTOR			
	Citizen of:		
Signature of Inventor	Post Office Address:		